OPA9420

Infrared LED Chip

GaAs/GaAs

1. Material

Substrate	GaAs	(N Type)
Epitaxial Layer	GaAs	(P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

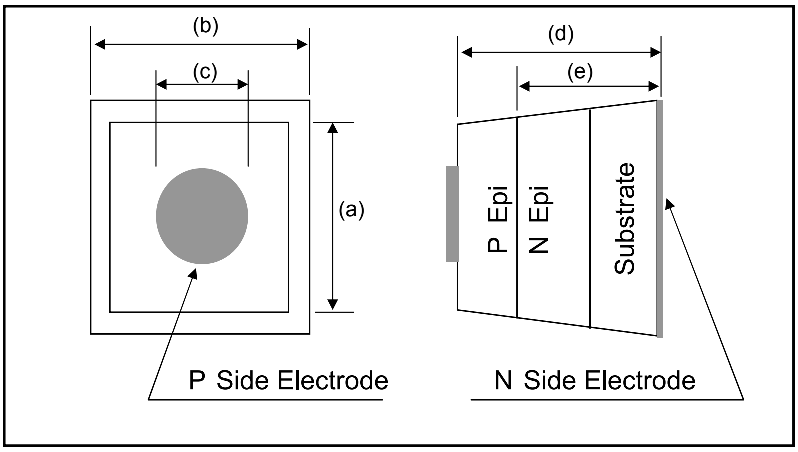
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.65	1.75	V	IF=100mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	11	21		mW	IF=100mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area	--------------------	7mil	x	7mil
(b) Bottom Area	--------------------	8mil	x	8mil
(c) Bonding Pad	--------------------	110um		
(d) Chip Thickness	--------------------	9.0mil		
(e) Junction Height	--------------------	6.5mil		



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